

SEC.626



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Seung-dong KANG et al.

Group Art Unit: 2814

Serial No. 09/275,808

Examiner: G. Peralta

Filed: March 25, 1999

For: Method of Fabricating a Capacitor

Assistant Commissioner of Patents  
Washington, D.C. 20231

Amdt  
4/A

12-10-99

T. Flowers

TO 2000 MAIL ROOM  
FEB-3 1999  
PROCESSED

**AMENDMENT UNDER 35 USC §1.111**

Sir:

In response to the Office Action of September 13, 1999, please amend the above-identified patent application as follows.

In the Claims:

Please amend claims 1, 7 and 14 as follows:

Claim 1. (Amended) A method for forming a capacitor electrode of a capacitor in a reacting chamber, the method comprising:

forming a first HSG nuclei by introducing a first amount of a source gas into the reacting chamber while an ambient temperature [stabilizes] is stabilizing within a first temperature range;

forming a second HSG nuclei over the first HSG nuclei by introducing a second amount of the source gas into the reacting chamber after the ambient temperature stabilizes within the first temperature range to form a resulting

Subst.  
B1

A1

Homispherical Silicon Graph

of the reaction chamber